

반도체공정개론 Homework solutions

Homework #1

1-a)

$$a) R = k_1 \frac{\lambda}{n \sin \theta} = k_1 \frac{\lambda}{NA}$$

이 식 사용해서 설명한 경우 모두 정답 처리

1-b)

EUV의 photon energy가 높아서 렌즈에 투과가 아닌 흡수가 되어 열이 발생, 렌즈에 damage 발생되기 때문

1-c)

다음 4가지만 정답 처리

- c) ① Double patterning
② phase shift masks
③ optical - proximity correction techniques
④ Double exposure

2-a)

a) $A = \text{area}$
 $V = \text{volume}$ $\leadsto V = Ax \text{ cm}^3$

$$\therefore \text{SiO}_2 (\text{g}) = 2.21 Ax (\text{g})$$

$$\text{SiO}_2 (\text{mol}) = \frac{2.21 Ax (\text{mol})}{60.08}$$

Si among SiO₂ (g)

$$= \frac{2.21 Ax \times 28.9 (\text{mol})}{60.08}$$

$$\therefore \text{Si} (\text{cm}^3) = \frac{2.21 Ax}{60.08} \times \frac{28.9}{2.33}$$

$$= 0.456 Ax \text{ cm}^3$$

A는 바뀌지 X
 $\therefore \text{SiO}_2$ 두께 1cm 0.456 Si layer
생김.

2-b)

0.7hr (그래프 보고 읽으면 됨, 이 외의 값은 오답)

Homework #2

1-a)

a) Table 1 $\rightarrow D_0 = 10.5 \text{ cm}^2/\text{s}$
 $E_A = 3.69 \text{ eV}$

$$D = 10.5 \exp\left(-\frac{3.69}{(8.614 \times 10^{-5})(1373)}\right)$$

$$= 2.96 \times 10^{-13} \text{ cm}^2/\text{s}$$

1-b)

b) Table 1 $\rightarrow D = 10.5 \exp\left(-\frac{3.69}{(8.614 \times 10^{-5})(1423)}\right)$

$$= 8.86 \times 10^{-13} \text{ cm}^2/\text{s}$$

$$(Dt)_{\text{tot}} = (2.96 \times 10^{-13} \text{ cm}^2/\text{s})(12000 \text{ s})$$

$$+ (8.86 \times 10^{-13} \text{ cm}^2/\text{s})(18000 \text{ s})$$

$$= 1.81 \times 10^{-8} \text{ cm}^2$$

1-c) (i)

c) i

C_s, x_j

Figure 2 \rightarrow boron is solid-solubility limited
 surface concentration
 $\sim 1.1 \times 10^{20} \text{ cm}^{-3}$

$$N(x) = 1.1 \times 10^{20} \operatorname{erfc}\left(\frac{x}{2\sqrt{Dt_i}}\right) \text{ boron atoms/cm}^3$$

Junction depth $x_j \Rightarrow N(x_j) = N_B$ (background concentration)
 \uparrow
 $3 \times 10^{16} \text{ cm}^{-3} \sim \text{Figure 3}$

$$\therefore 1.1 \times 10^{20} \operatorname{erfc}\left(\frac{x_j}{2\sqrt{Dt_i}}\right) = 3 \times 10^{16}$$

$$x_j = 2\sqrt{Dt_i} \operatorname{erfc}^{-1}(0.000213)$$

$\sim \text{Figure 1}$

$$= 2\sqrt{1.31 \times 10^{-12}} (2.57) \text{ cm}$$

$$= 0.0587 \text{ } \mu\text{m} \quad (58.7 \text{ nm})$$

1-c) (ii)

c) ii

$$Q = 2N_0 \sqrt{Dt_i} / \pi = 2(1.1 \times 10^{20}) \sqrt{(1.45 \times 10^{-15}) / \pi}$$

$$\therefore Q = 1.42 \times 10^{14} \text{ boron atoms/cm}^2$$

$$N(x) = \frac{Q}{\sqrt{\pi Dt_2}} \exp\left(-\frac{x_j^2}{4Dt_2}\right)$$

$$= 1.1 \times 10^{18} \exp\left(-\frac{x_j^2}{1.47 \times 10^{-4}}\right)$$

$$N_B = 3 \times 10^{16} \sim \text{Figure 3}$$

$$\therefore 1.1 \times 10^{18} \exp\left(-\frac{x_j^2}{1.47 \times 10^{-4}}\right) = 3 \times 10^{16}$$

i) 문제와 같은 방법으로 풀이함.

$$x_j = 1.41 \times 10^{-4} \times \sqrt{\ln\left(\frac{1.1 \times 10^{18}}{3 \times 10^{16}}\right)}$$

$$= 2.77 \text{ } \mu\text{m}$$

2)

$$10 \text{ } \mu\text{m} = W - 2(300 \text{ } \mu\text{m}) \cot(54.7^\circ)$$

$$10 \text{ } \mu\text{m} \approx W - \sqrt{2} \times (300 \text{ } \mu\text{m})$$

$$W = 434.26 \text{ } \mu\text{m}$$